
HVU133

Silicon Epitaxial Planar Pin Diode for High Frequency Switching

HITACHI

ADE-208-377A(Z)

Rev 1

September 1996

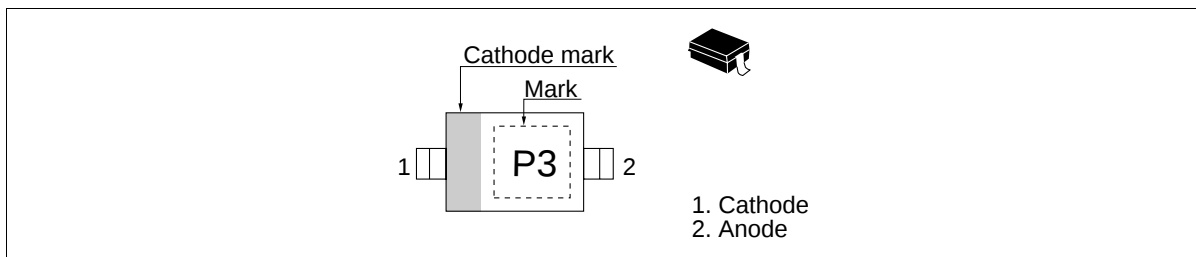
Features

- Low capacitance.(C1=1.0pF max)
- Low forward resistance. ($r_f=0.7\Omega$ max)
- Ultra small Resin Package (URP) is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HVU133	P3	URP

Outline



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Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Reverse voltage	VR	30	V
Power dissipation	Pd	150	mW
Junction temperature	TJ	125	°C
Storage temperature	Tstg	-55~+125	°C

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse voltage	VR	30	~	~	V	IR = 1μA
Reverse current	IR	~	~	100	nA	VR = 25V
Forward voltage	VF	~	~	0.85	V	IF = 2 mA
Capacitance	C1	~	~	1.0	pF	VR = 1V, f = 1 MHz
	C6	~	~	0.9		VR = 6V, f = 1 MHz
Forward resistance	rf	~	0.55	0.7	Ω	IF = 2mA, f = 100 MHz

Main Characteristic

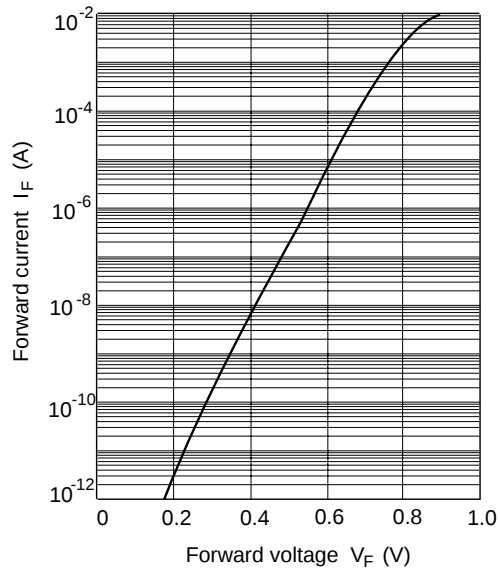


Fig.1 Forward current Vs. Forward voltage

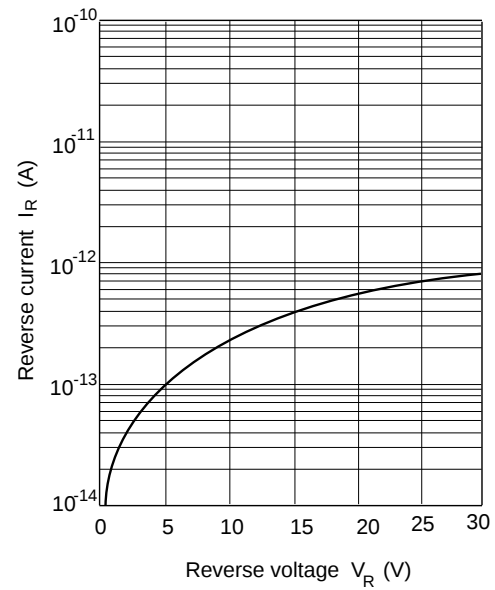


Fig.2 Reverse current Vs. Reverse voltage

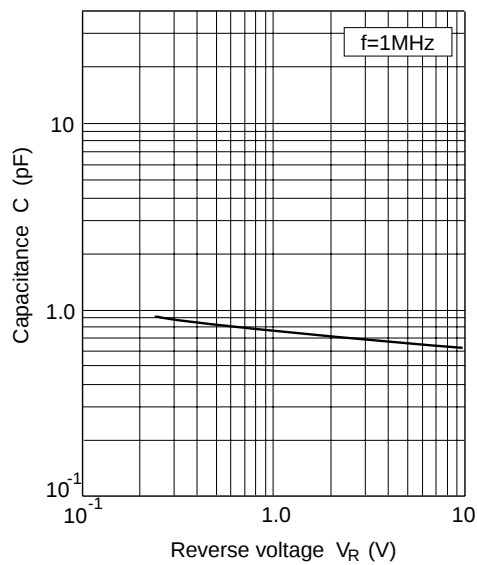


Fig.3 Capacitance Vs. Reverse voltage

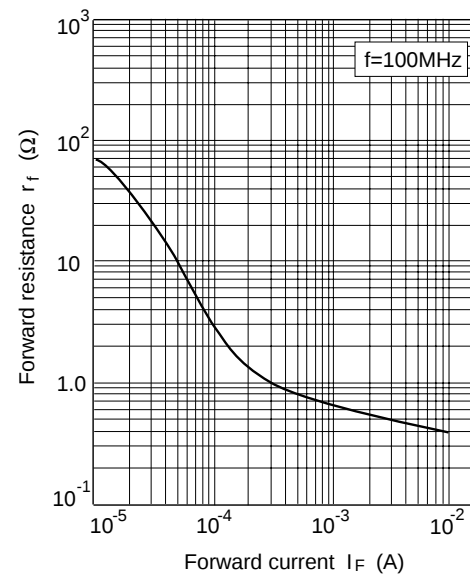


Fig.4 Forward resistance Vs. Forward current

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Package Dimensions

Unit : mm

